TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2 S A 1 1 4 5

AUDIO FREQUENCY AMPLIFIER APPLICATIONS.

Complementary to 2SC2705.

Small Collector Output Capacitance : Cob=2.5pF (Typ.)

: $f_T = 200 MHz (Typ.)$ High Transition Frequency

MAXIMUM RATINGS ($Ta = 25^{\circ}C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	-150	V
Collector-Emitter Voltage	v_{CEO}	_150	v
Emitter-Base Voltage	$V_{ m EBO}$	- 5	V
Collector Current	$I_{\mathbf{C}}$	-50	mA
Base Current	$I_{\mathbf{B}}$	-5	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	800	mW
Junction Temperature	T_{j}	150	°C
Storage Temperature Range	$T_{ m stg}$	-55~150	°C

Unit in mm 5.1 MAX 0.75MAX 1.0 MAX 0.8 MAX 0.6 MAX 1.1 MAX **EMITTER** COLLECTOR 3. BASE **JEDEC** TO-92MOD **EIAJ TOSHIBA** 2-5J1A

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

ELECTRICAL CHARACTERISTICS (Ta = 25°C)		Wei	Weight: 0.36g			
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -150V, I_{E} = 0$	_	_	-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_{C} = 0$	_	_	-0.1	μ A
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	$I_C = -1$ mA, $I_B = 0$	-150	_	_	V
DC Current Gain	hFE (Note)	$V_{CE} = -5V, I_{C} = -10mA$	80	_	240	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	$I_C = -10 \text{mA}, I_B = -1 \text{mA}$	_	_	-1.0	V
Base-Emitter Voltage	$ m v_{BE}$	$V_{CE} = -5V, I_{C} = -10mA$		_	-0.8	V
Transition Frequency	$ m f_{T}$	$V_{CE} = -10V, I_{C} = -10mA$	_	200	_	MHz
Collector Output Capacitance	C _{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	_	2.5	_	pF

Note: hFE Classification $O: 80\sim160, Y: 120\sim240$

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